

IN THE CLAIMS:

1. (Currently Amended) A semiconductor light emitting device comprising:

a substrate;

a plurality of semiconductor blue-light first-light emitting elements each having an epitaxial structure member that is formed on the substrate in an epitaxial growth on the

5 substrate step of a wafer fabrication process;

a plurality of pairs of pads that are on the substrate and together with the semiconductor blue-light emitting elements, arranged in a matrix, in such a manner that each pair of pads is adjacent to a different one of the semiconductor blue-light emitting elements in a row and column direction an electrically conductive pattern that is formed on the substrate in a wiring

10 step of the wafer fabrication process; and

a plurality of semiconductor red-light second-light emitting elements that are each member that is separately formed and then mounted on a different one of the pairs of pads, wherein a height of each semiconductor red-light emitting element from the substrate is greater than a height of each semiconductor blue-light emitting element from the substrate the
15 electrically conductive pattern, the second-light emitting member emitting light of a different color from the first light emitting member.

2. - 3. (Cancelled)

4. (Currently Amended) The semiconductor light emitting device of Claim 1 Claim 3, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:

a phosphor that covers the blue LEDs and the red LEDs and converts blue light
5 emitted by the blue LEDs into green-yellow light.

~~each of the plurality of first light emitting elements is one of a red LED and a blue
LED, and each of the plurality of second light emitting elements is a different one of the red
LED and the blue LED, and~~

~~the semiconductor light emitting device further comprises:~~

10 ~~a phosphor that covers a plurality of red LEDs and a plurality of blue LEDs, the
phosphor converting blue light emitted by the plurality of blue LEDs into green-yellow light.~~

5. (Currently Amended) The semiconductor light emitting device of Claim 4,
wherein the red light, which is emitted by the red LEDs, has a peak emission wavelength within
a range of 615 nm and 635 nm,

the blue light has a peak emission wavelength within a range of 450 nm and 470
5 nm, and

the green-yellow light has a peak emission wavelength within a range of 540 nm
and 560 nm.

6. (Original) The semiconductor light emitting device of Claim 5, wherein
the red light has a peak emission wavelength within a range of 620 nm and 630
nm,

the blue light has a peak emission wavelength within a range of 455 nm and 465
5 nm, and

the green-yellow light has a peak emission wavelength within a range of 545 nm
and 555 nm.

7. (Original) The semiconductor light emitting device of Claim 4, wherein the phosphor is a silicate phosphor $(\text{Ba, Sr})_2\text{SiO}_4:\text{Eu}^{2+}$.

8. (Original) The semiconductor light emitting device of Claim 4, wherein the substrate is made of one of SiC and AlN materials.

9. (Currently Amended) The semiconductor light emitting device of Claim 4 Claim 2, further comprising:

a wiring pattern that ~~is formed on the substrate in the wiring step of the wafer fabrication process, the wiring pattern~~ electrically connects the blue LEDs and the red LEDs
5 ~~connecting the plurality of first light emitting elements and the plurality of second light emitting elements together.~~

10. (Currently Amended) The semiconductor light emitting device of Claim 9, wherein

the wiring pattern connects the blue LEDs and the red LEDs together ~~plurality of first light emitting elements and the plurality of second light emitting elements~~ in series.

11.-15. (Cancelled)

16. (Currently Amended) A light emitting module comprising:

a printed-wiring board; and

a semiconductor light emitting device including:

a substrate;

5 a plurality of semiconductor blue-light emitting elements each having an epitaxial structure on the substrate;

a plurality of pairs of pads that are on the substrate and together with the semiconductor blue-light emitting elements, arranged in a matrix, in such a manner that each pair of pads is adjacent to a different one of the semiconductor blue-light emitting elements in a row
10 and column direction; and

a plurality of semiconductor red-light emitting elements that are each mounted on a different one of the pairs of pads, wherein a height of each semiconductor red-light element from the substrate is greater than a height of each semiconductor blue-light emitting element from the substrate, that is claimed in Claim 1 and is mounted on the printed-wiring board.

17. (Currently Amended) The light emitting module of Claim 16, A lighting apparatus comprising further comprising:

a lighting apparatus including a closed structure in which the light emitting module is disposed a light emitting module claimed in Claim 16.

18. (New) The light emitting module of Claim 16, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:

 a phosphor that covers the blue LEDs and the red LEDs and converts blue light
5 emitted by the blue LEDs into green-yellow light.

19. (New) The light emitting module of Claim 18, wherein red light, which is emitted by the red LEDs, has a peak emission wavelength within a range of 615 nm and 635 nm,

the blue light has a peak emission wavelength within a range of 450 nm and 470 nm, and

5 the green-yellow light has a peak emission wavelength within a range of 540 nm and 560 nm.

20. (New) The light emitting module of Claim 18, wherein the red light has a peak emission wavelength within a range of 620 nm and 630 nm,

the blue light has a peak emission wavelength within a range of 455 nm and 465 nm, and

5 the green-yellow light has a peak emission wavelength within a range of 545 nm and 555 nm.

21. (New) The light emitting module of Claim 18, wherein the phosphor is a silicate phosphor $(\text{Ba, Sr})_2\text{SiO}_4:\text{Eu}^{2+}$.

22. (New) The light emitting module of Claim 16, wherein the substrate is made of one of SiC and AlN materials.

23. (New) The light emitting module of Claim 16, further comprising:
a wiring pattern that electrically connects the blue LEDs and the red LEDs together.

24. (New) The light emitting module of Claim 23, wherein the wiring pattern connects the blue LEDs and the red LEDs together in series.

25. (New) A method for manufacturing a semiconductor light emitting device comprising:

providing a substrate;

growing a plurality of semiconductor blue-light emitting elements on the substrate

5 with an epitaxial structure;

forming a plurality of pairs of pads on the substrate in such a manner that each pair of pads is adjacent to a different one of the semiconductor blue-light emitting elements in a row and column direction; and

10 mounting a plurality of semiconductor red-light emitting elements on a different one of the pairs of pads, wherein a height of each semiconductor red-light emitting element from the substrate is greater than a height of each semiconductor blue-light emitting element from the substrate.

26. (New) The method of Claim 25, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:

5 covering the blue LEDs and the red LEDs with a phosphor that converts blue light emitted by the blue LEDs into green-yellow light.

27. (New) The method of Claim 25, further comprising:

forming a wiring pattern that electrically connects the blue LEDs and the red LEDs together.